

37 CFR 1.501  
 INFORMATION DISCLOSURE STATEMENT  
 IN A PATENT  
 (use several sheets if necessary)

Docket No.  
P97,0027Serial No.  
08/818,239Applicant  
Hiroshi TayanakaFiling Date  
March 14, 1997Group Art Unit  
2813

## U.S. PATENT DOCUMENTS

| Examiner's Initials |    | Document Number | Date     | Name              | Class | Subclass | Filing Date If appropriate |
|---------------------|----|-----------------|----------|-------------------|-------|----------|----------------------------|
| YC                  | AA | 4,727,047       | 02-23-88 | Bozler, et al.    | —     | —        |                            |
| YC                  | AB | 5,854,123       | 12-29-98 | Sato, et al.      | —     | —        |                            |
| YC                  | AC | 5,856,229       | 01-05-99 | Sakaguchi, et al. | —     | —        |                            |
| —                   | AD |                 |          |                   |       |          | RECEIVED                   |
| —                   | AE |                 |          |                   |       |          | FFB 22 2000                |
| —                   | AF |                 |          |                   |       |          |                            |
| —                   | AG |                 |          |                   |       |          | TECHNOLOGY CENTER 2800     |
| —                   | AH |                 |          |                   |       |          |                            |
| —                   | AI |                 |          |                   |       |          |                            |
| —                   | AJ |                 |          |                   |       |          |                            |
| —                   | AK |                 |          |                   |       |          |                            |

## FOREIGN PATENT DOCUMENTS

|    |    | Document Number |          | Country |   | Translation |          |    |
|----|----|-----------------|----------|---------|---|-------------|----------|----|
|    |    |                 |          |         |   |             | Yes      | No |
| YC | AL | JP62-279625     | 12-04-87 | Japan   | — | —           | Abstract | X  |
| —  | AM |                 |          |         |   |             |          |    |
| —  | AN |                 |          |         |   |             |          |    |
| —  | AO |                 |          |         |   |             |          |    |
| —  | AP |                 |          |         |   |             |          |    |
| —  | AQ |                 |          |         |   |             |          |    |
| —  | AR |                 |          |         |   |             |          |    |
| —  | AS |                 |          |         |   |             |          |    |

## OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)

|                                   |    |  |
|-----------------------------------|----|--|
| YC                                | AT | V. Labunov, et al., "Heat Treatment Effect on Porous Silicon", Thin Solid Films, Vol. 137, pp. 123-134 1986  |
| YC                                | AU | N. Sato, et al., "Epitaxial Growth on Porous Si for a New Bond and Etch-back SOI", The Electrochemical Society, Spring Meeting, May 22-27, 1994, Extended Abstracts, Vol. 94-1, Abstract No 443, pp. 705-706 |
| <i>no translation explanation</i> | AV | "Crystalline Silicon and Doping", Maruzen Kabushiki Kaisha Publisher, 1986   |
| —                                 | AW |  |
| —                                 | AX |  |
| —                                 | AY |  |

Examiner YCDate Considered 6/5/2000

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.